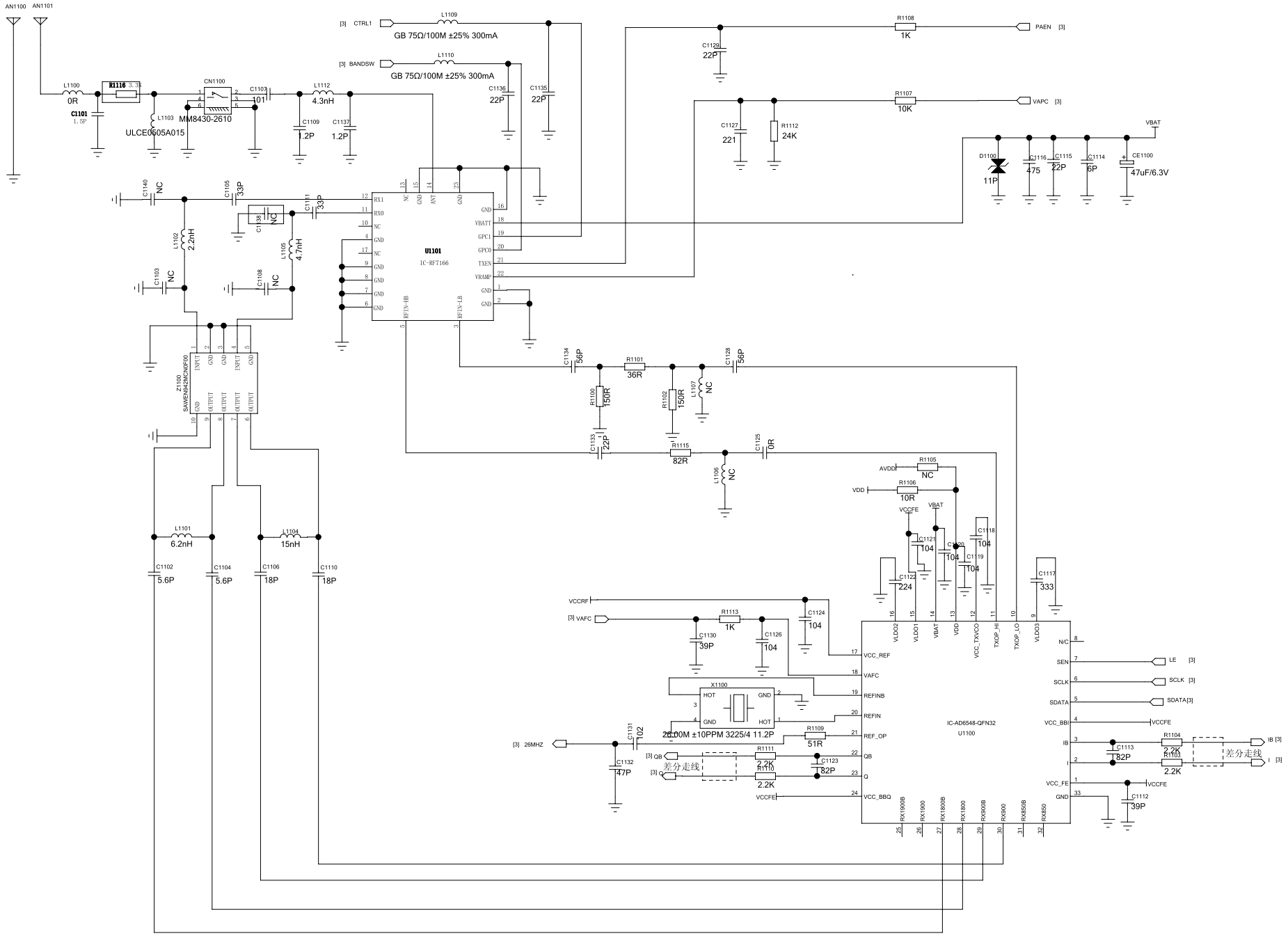
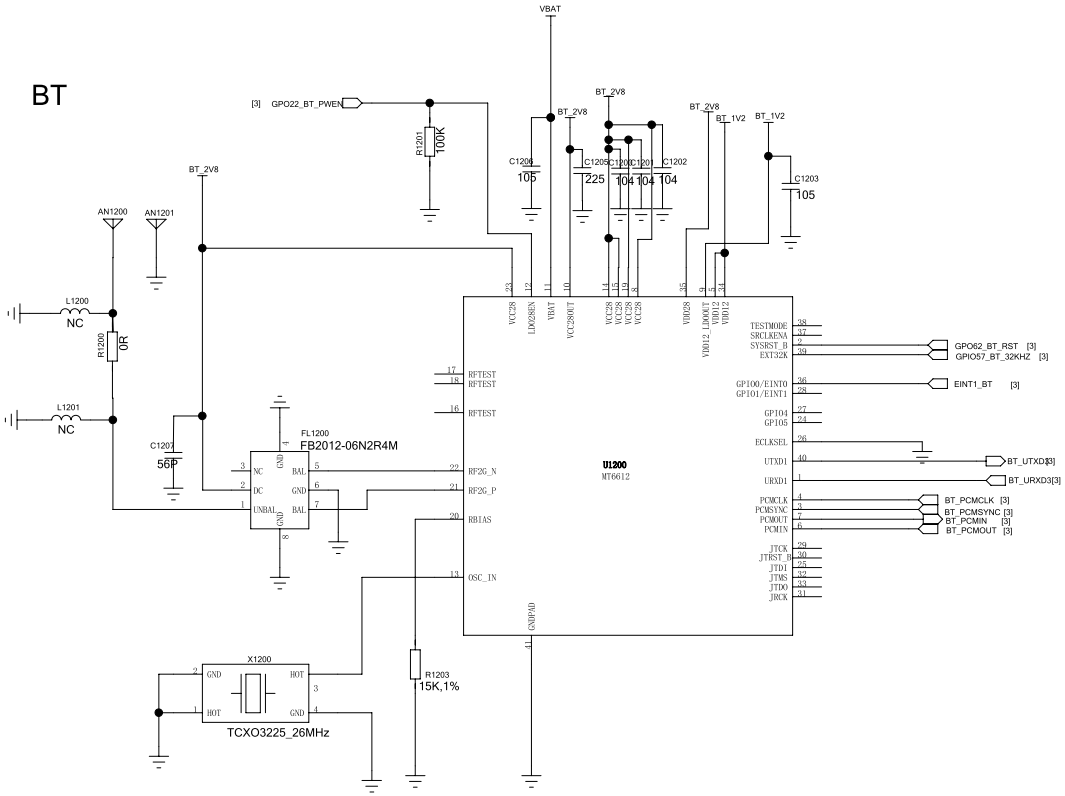
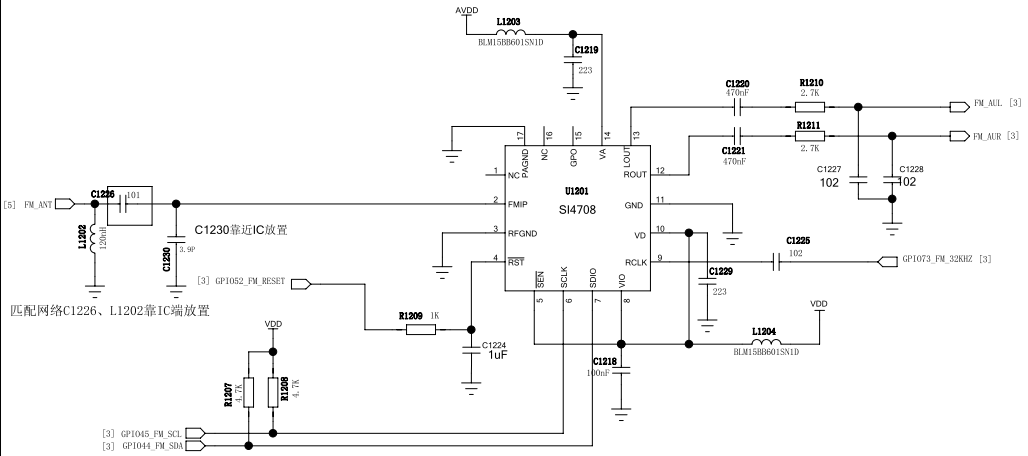

AN1100
AN1101
L1100 0R
R1116 0.3R
C1101 1.5P
CN1100
MM8430-2610
L1103 ULCE0605A015
C1107 101
L1112 4.3nH
C1109 1.2P
C1137 1.2P
[3] CTRL1
L1109 GB 75Ω/100M ±25% 300mA
[3] BANDSW
L1110 GB 75Ω/100M ±25% 300mA
C1136 22P
C1135 22P
C1129 22P
R1108 1K
PAEN [3]
R1107 10K
VAPC [3]
C1127 221
R1112 24K
VBAT
D1100 11P
C1116 475
C1115 22P
C1114 6P
CE1100 47uF/6.3V
C1140 NC
C1105 33P
C1138 NC
C1111 33P
L1102 2.2nH
L1105 4.7nH
C1103 NC
C1108 NC
U1101
IC-RF7166
RX1
RX0
GND
VBATT
GPC1
GPC0
TXEN
VRAMP
RFIN-HB
RFIN-LB
Z1100
SAWEN842MCN0F00
C1134 56P
R1101 36R
C1128 56P
R1100 150R
R1102 150R
L1107 NC
C1133 22P
R1115 82R
C1125 0R
L1106 NC
R1105 NC
R1106 10R
AVDD
VDD
VCCFE
VBAT
C1121 104
C1120 104
C1119 104
C1118 104
C1122 224
C1117 333
L1101 6.2nH
L1104 15nH
C1102 5.6P
C1104 5.6P
C1106 18P
C1110 18P
VCCRF
[3] VAFC
R1113 1K
C1130 39P
C1126 104
C1124 104
X1100
26.00M ±10PPM 3225/4 11.2P
[3] 26MHZ
C1131 102
C1132 47P
R1109 51R
R1111 2.2K
R1110 2.2K
C1123 82P
差分走线
[3] QB
[3] Q
VCCFE
IC-AD6548-QFN32
U1100
VCC_REF
VAFC
REFINB
REFIN
REF_OP
QB
Q
VCC_BBQ
VLDO2
VLDO1
VBAT
VDD
VCC_TXVCO
TXOP_HI
TXOP_LO
VLDO3
N/C
SEN
SCLK
SDATA
VCC_BBI
IB
VCC_FE
GND
LE [3]
SCLK [3]
SDATA[3]
VCCFE
R1104 2.2K
R1103 2.2K
C1113 82P
C1112 39P
IB [3]
I [3]
RX1900B
RX1900
RX1800B
RX1800
RX900B
RX900
RX850B
RX850

0 PP0 A 115K

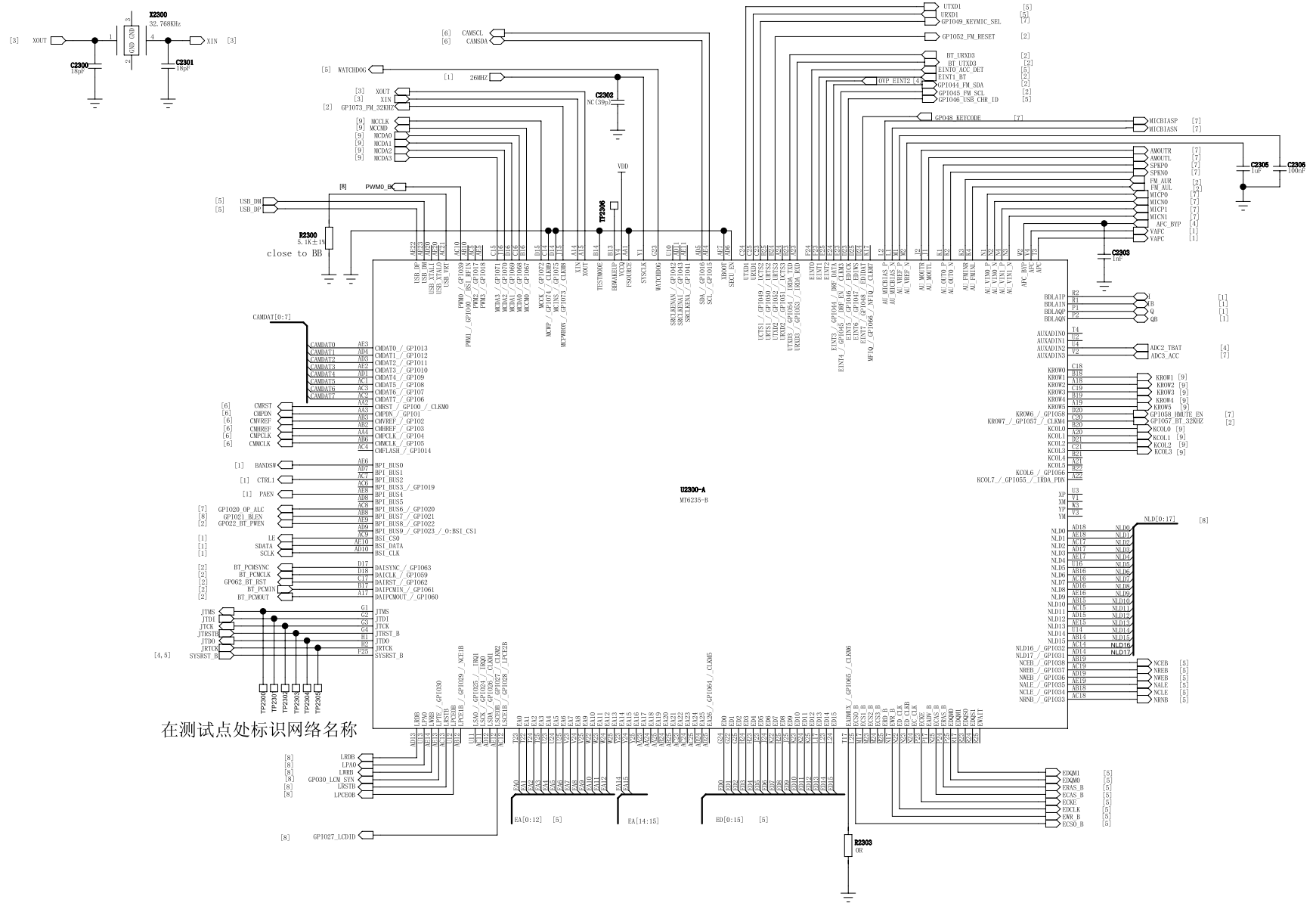
BT



FM



OPPO A115K


X2300
32.768KHz
C2300
18pF
C2301
18pF
C2302
NC(39p)
C2303
1nF
C2305
1uF
C2306
100nF
R2300
5.1K±1%
close to BB
R2303
0R
TP2306
U2300-A
MT6235-B
在测试点处标识网络名称

PMU

	Power	Vout (V)	Max current (mA)	Output capacitor (F)
VCORE	VCORE	1.2(DC/DC)	350	4.7u
VMEM	VM	1.8	300	4.7u
CM_2V8	VCAM_A	2.8	250	4.7u
CM_1V8	VCAM_D	1.8	75	1u
VCCRF	VRF	2.8	350	4.7u
AVDD	VA	2.8	125	4.7u
VTCXO	VTCXO	2.8	40	1u
VDD	VIO	2.8	100	1u
AVDDBUF	VBT	2.8	100	1u
VUSB	VUSB	3.3	75	1u
VSIM_A	VSIM	1.8/3.0	80	1u
	VSIM_2	1.8/3.0	80	1u
VRTC	VRTC	3.3	0.02	100n
VBT	VBT	2.8	100	1u

VRTC、VSIM、VTCXO：10mil at least
VCORE：25mil at least
VDD、AVDD、VMEM:20mil at least
VCHG、VBAT:40mil at least

CAM_2V8,VCCRF反馈点尽量从负载端取

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差分线

BAT-CON

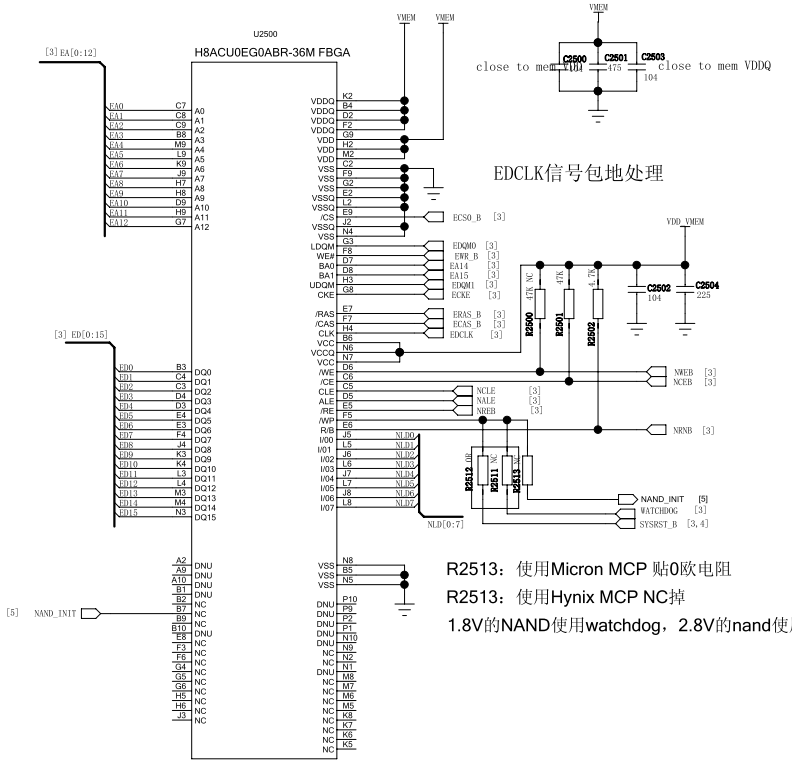
一个放连接器旁，一个放测试点旁

OVP

加粗充电回路走线

PESD5V0V1BL::5V 11P

1Gb NAND FLASH + 256Mb MOBILE SDRAM

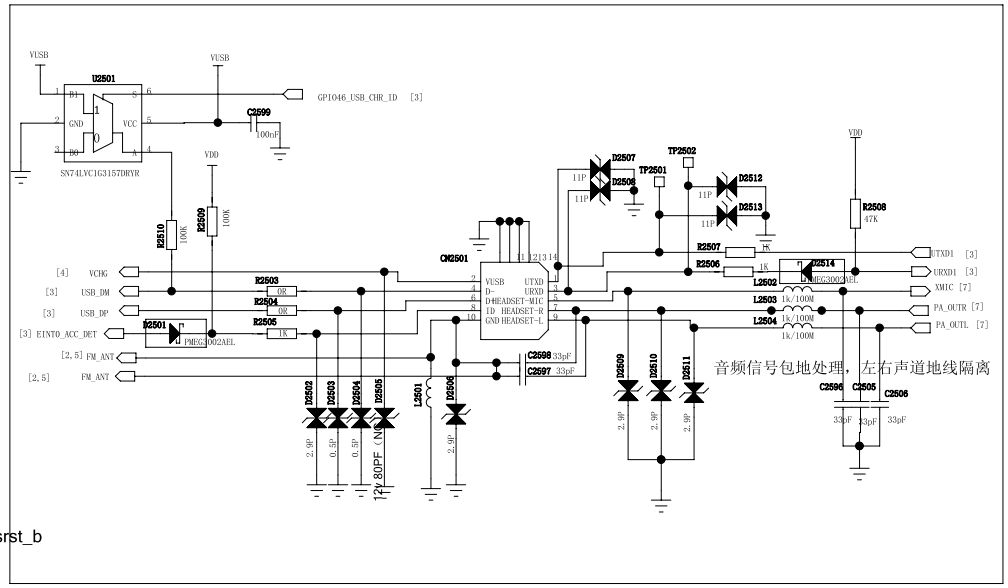


EDCLK信号包地处理

R2513：使用Micron MCP 贴0欧电阻

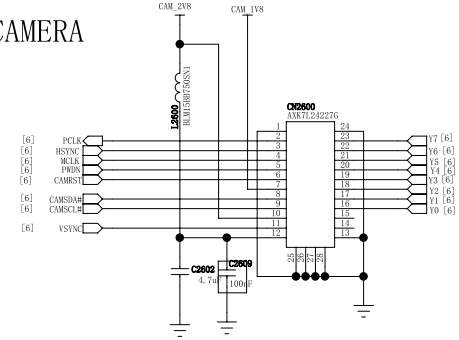
R2513：使用Hynix MCP NC掉

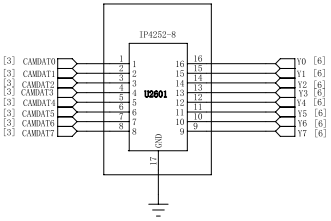
1.8V的NAND使用watchdog，2.8V的nand使用sysrst_b

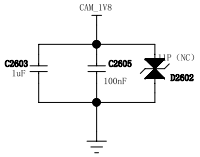


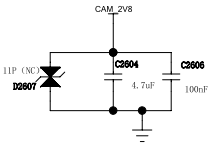
音频信号包地处理，左右声道地线隔离

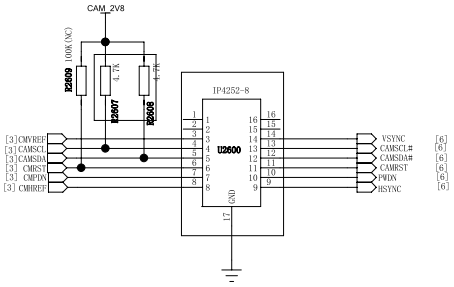
CAMERA

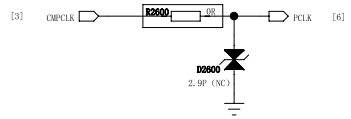


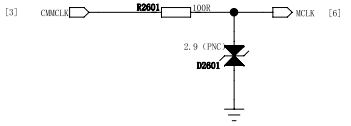










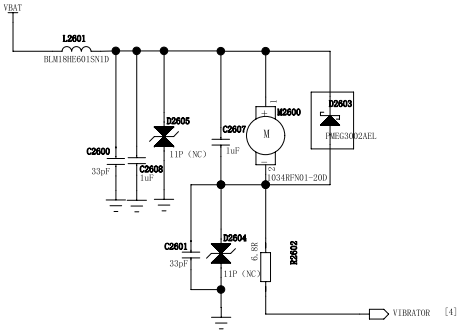


CAMERA PIN ASSIGNMENTS

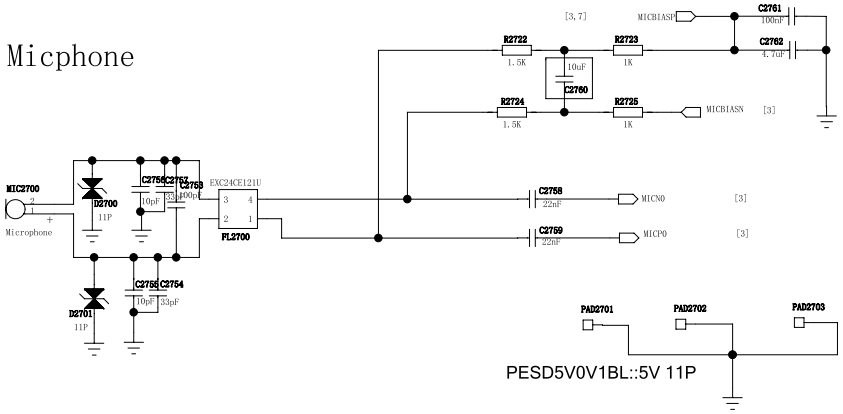
1	GND	24	GND
2	PCLK	23	Y7
3	HSYNC	22	Y6
4	MCLK	21	Y5
5	STANDBY	20	Y4
6	RESETB	19	Y3
7	DVDD_1.8V (CORE)	18	Y2
8	SDA	17	Y1
9	SCL	16	Y0
10	VDDIO_2.8V	15	NC
11	VSYNC	14	NC
12	AVDD_2.8V(ANALOG)	13	GND

PCLK/MCLK:keep 8mil distance
against other traces

VIB

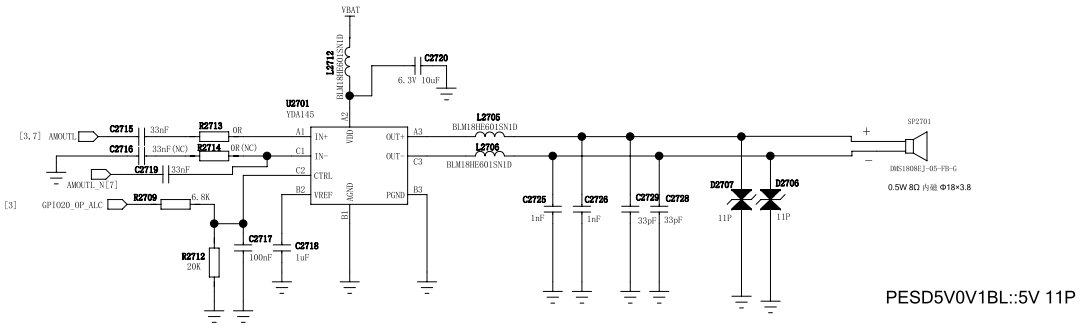


Micphone

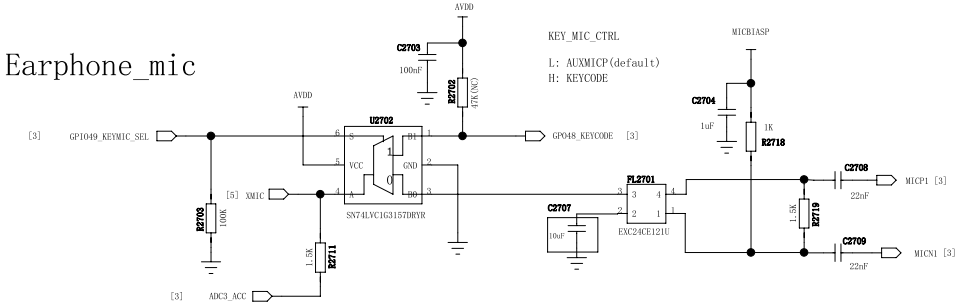


Loud Speaker

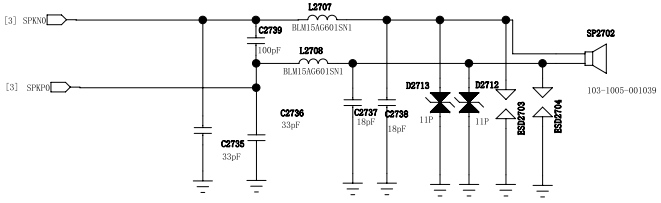
0 PP0 A 115K

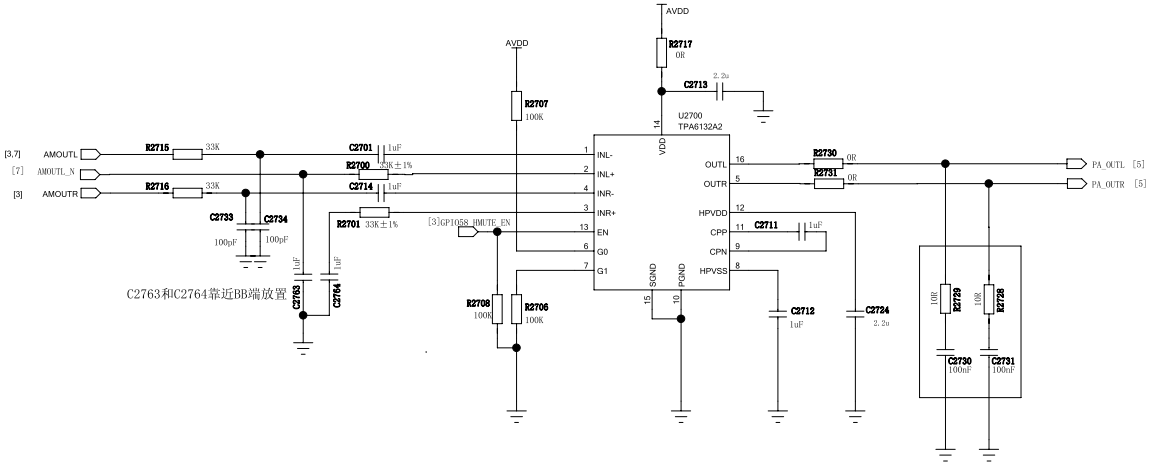


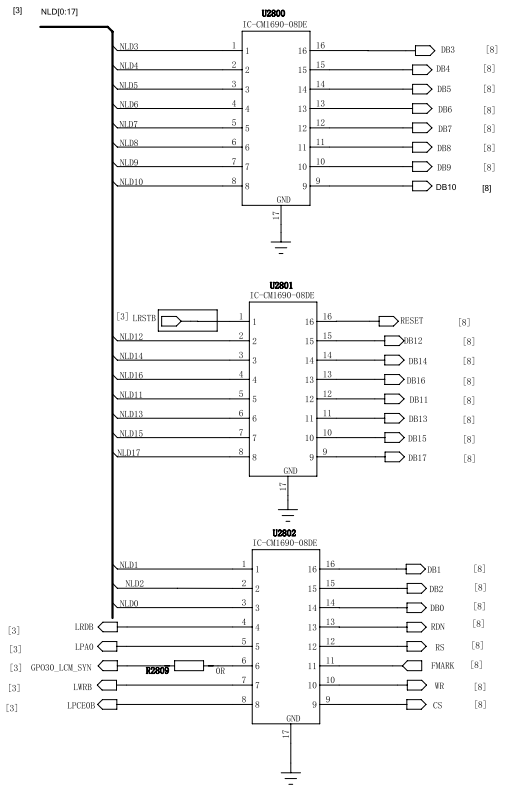
Earphone_mic

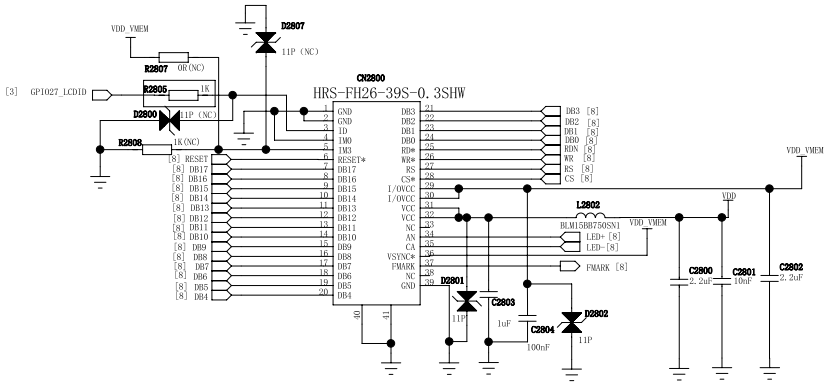


Receiver



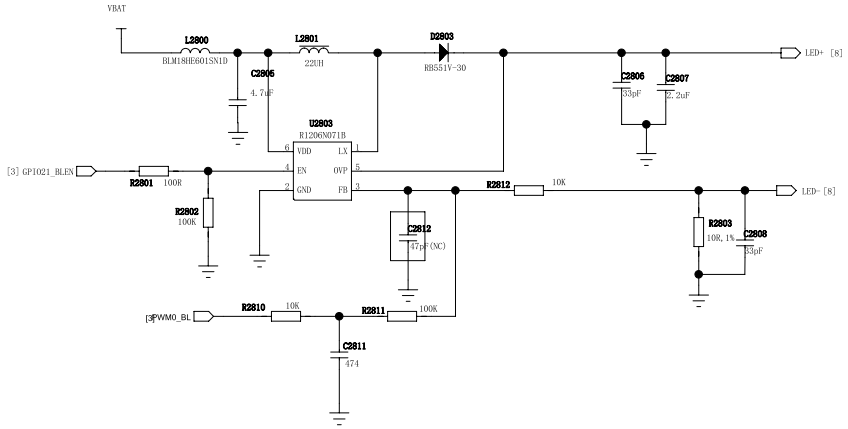




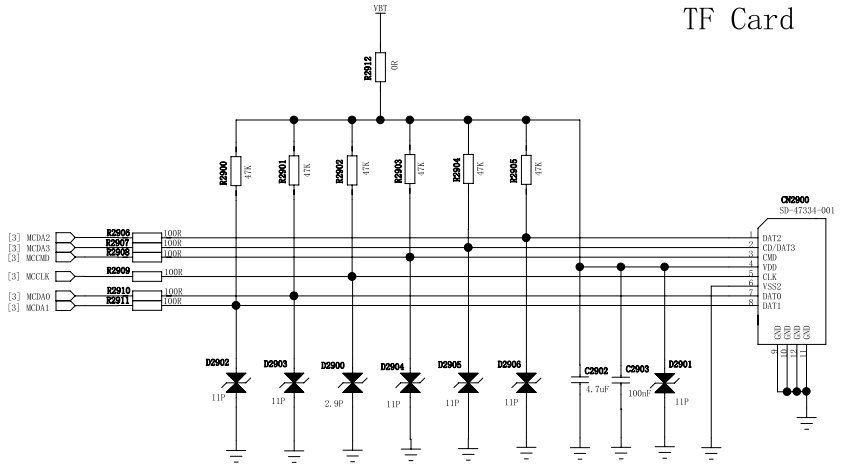


PESD5V0V1BL::5V 11P

BACKLIGHT



TF Card



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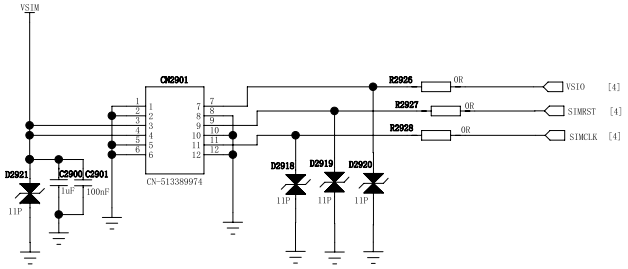
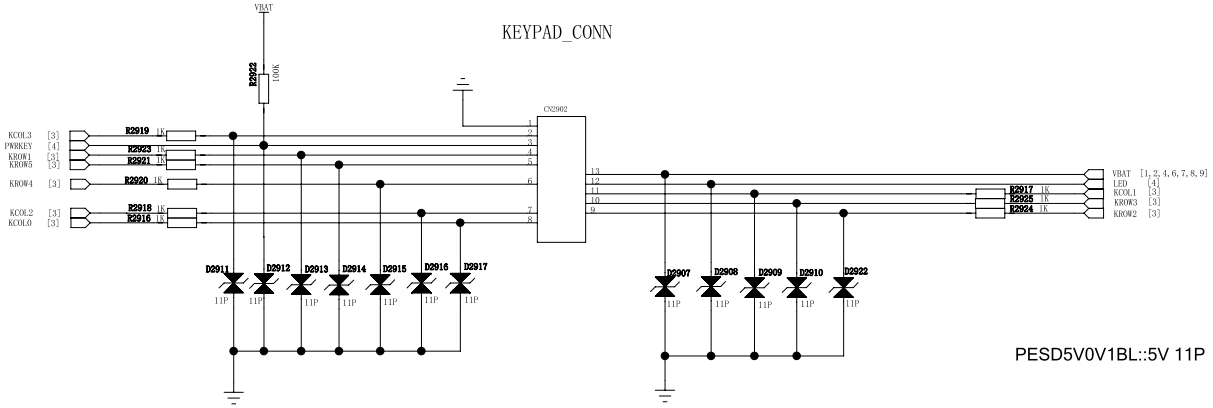
SIM Card Connector



PESD5V0V1BL::5V 11P

KEYPAD_CONN



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